MOSFETs Silicon P-Channel MOS

# SSM6P49NU

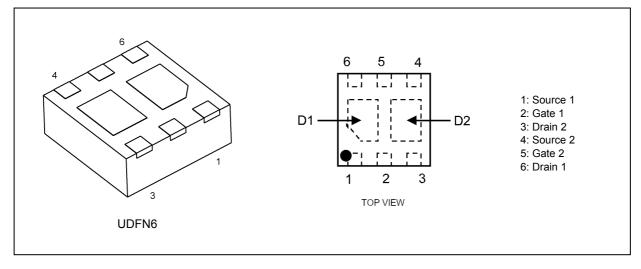
### 1. Applications

Power Management Switches

### 2. Features

- (1) 1.8 V drive
- (2) Low drain-source on-resistance
  - $\begin{array}{l} : \mathrm{R}_{\mathrm{DS(ON)}} = 157 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -1.8 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 76 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -2.5 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 56 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -4.5 \ \mathrm{V}) \\ \mathrm{R}_{\mathrm{DS(ON)}} = 45 \ \mathrm{m}\Omega \ (\mathrm{max}) \ (@\mathrm{V}_{\mathrm{GS}} = -10 \ \mathrm{V}) \end{array}$

## 3. Packaging and Pin Assignment



#### Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 ℃)(Q1, Q2 Common)

|                        | Characteristics |          |                    | Symbol           | Rating     | Unit |
|------------------------|-----------------|----------|--------------------|------------------|------------|------|
| Drain-source voltage   |                 |          |                    | V <sub>DSS</sub> | -20        | V    |
| Gate-source voltage    |                 |          |                    | V <sub>GSS</sub> | ±12        |      |
| Drain current (DC)     |                 |          | (Note 1)           | Ι <sub>D</sub>   | -4         | А    |
| Drain current (pulsed) |                 |          | (Note 1), (Note 2) | I <sub>DP</sub>  | -16        | 1    |
| Power dissipation      |                 |          | (Note 3)           | PD               | 1          | w    |
| Power dissipation      | (t              | i≤ 10 s) | (Note 3)           |                  | 2          | 1    |
| Channel temperature    |                 |          |                    | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature    |                 |          |                    | T <sub>stg</sub> | -55 to 150 |      |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  100  $\mu s,\,duty \leq$  1 %
- Note 3: Device mounted on a FR4 board. (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu pad: 645 mm²)
- Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Thermal Characteristics

| Characteristics                       |          | Symbol                | Max | Unit |
|---------------------------------------|----------|-----------------------|-----|------|
| Channel-to-ambient thermal resistance | (Note 1) | R <sub>th(ch-a)</sub> | 125 | °C/W |

Note 1: Device mounted on an 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)

## 6. Electrical Characteristics

#### 6.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

| Characteristics                |          | Symbol               | Test Condition                                    | Min  | Тур. | Max  | Unit |
|--------------------------------|----------|----------------------|---------------------------------------------------|------|------|------|------|
| Gate leakage current           |          | I <sub>GSS</sub>     | $V_{DS}$ = 0 V, $V_{GS}$ = ±10 V                  |      | _    | ±1   | μA   |
| Drain cut-off current          |          | I <sub>DSS</sub>     | V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V    |      |      | -1   |      |
| Drain-source breakdown voltage |          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V     | -20  | —    | _    | V    |
| Drain-source breakdown voltage | (Note 1) | V <sub>(BR)DSX</sub> | I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 8 V     | -12  | _    | _    |      |
| Gate threshold voltage         | (Note 2) | V <sub>th</sub>      | V <sub>DS</sub> = -3 V, I <sub>D</sub> = -1 mA    | -0.5 | —    | -1.2 |      |
| Drain-source on-resistance     | (Note 3) | R <sub>DS(ON)</sub>  | $I_D$ = -0.5 A, $V_{GS}$ = -1.8 V                 | —    | 83   | 157  | mΩ   |
|                                |          |                      | I <sub>D</sub> = -2.0 A, V <sub>GS</sub> = -2.5 V |      | 60   | 76   |      |
|                                |          |                      | I <sub>D</sub> = -3.0 A, V <sub>GS</sub> = -4.5 V |      | 44   | 56   |      |
|                                |          |                      | I <sub>D</sub> = -3.5 A, V <sub>GS</sub> = -10 V  |      | 36   | 45   |      |
| Forward transfer admittance    | (Note 3) | Y <sub>fs</sub>      | V <sub>DS</sub> = -3 V, I <sub>D</sub> = -2.0 A   | 4.7  | 9.5  | _    | S    |

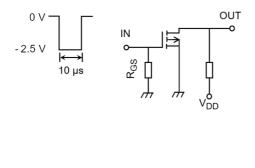
Note 1: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 3: Pulse measurement.

#### 6.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 ℃)(Q1, Q2 Common)

| Characteristics                | Symbol           | Test Condition                                                                                                          | Min | Тур. | Max | Unit |
|--------------------------------|------------------|-------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | $V_{DS}$ = -10 V , $V_{GS}$ = 0 V,                                                                                      | —   | 480  | —   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> | f = 1 MHz                                                                                                               | _   | 76   | —   |      |
| Output capacitance             | C <sub>oss</sub> |                                                                                                                         | _   | 90   | _   |      |
| Switching time (turn-on time)  | t <sub>on</sub>  | V <sub>DD</sub> = -10 V, I <sub>D</sub> = -0.5 A,<br>V <sub>GS</sub> = 0 to -2.5 V, R <sub>GS</sub> = 4.7 Ω,            |     | 21   |     | ns   |
| Switching time (turn-off time) | t <sub>off</sub> | $\begin{array}{l} Duty \leq 1 \ \%, V_{IN}: t_r,  t_f < 5 \ ns, \\ Common \ source, \ See \ Chapter \ 6.3. \end{array}$ |     | 54   |     |      |

## 6.3. Switching Time Test Circuit



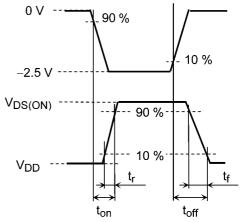


Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

#### 6.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 ℃)(Q1, Q2 Common)

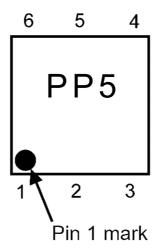
| Characteristics                                 | Symbol           | Test Condition                                    | Min | Тур. | Max | Unit |
|-------------------------------------------------|------------------|---------------------------------------------------|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | V <sub>DD</sub> = -10 V, I <sub>D</sub> = -4.0 A, | _   | 6.74 |     | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> | V <sub>GS</sub> = -4.5 V                          | _   | 0.95 | _   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |                                                   |     | 1.50 | _   |      |

#### 6.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

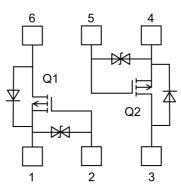
| Characteristics       |          | Symbol           | Test Condition                   | Min | Тур. | Max | Unit |
|-----------------------|----------|------------------|----------------------------------|-----|------|-----|------|
| Diode forward voltage | (Note 1) | $V_{\text{DSF}}$ | $I_{DR}$ = 4.0 A, $V_{GS}$ = 0 V | _   | 0.87 | 1.2 | V    |

Note 1: Pulse measurement.

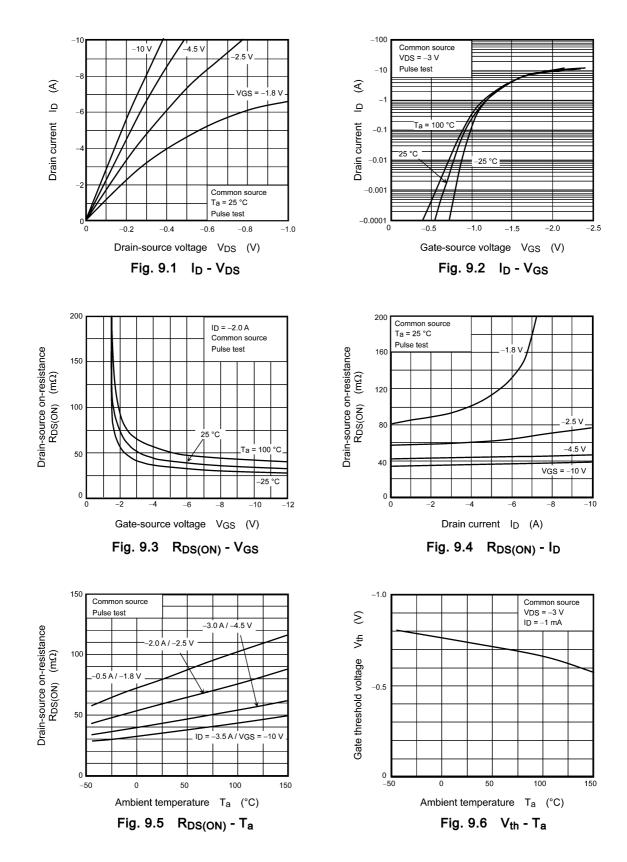
### 7. Marking

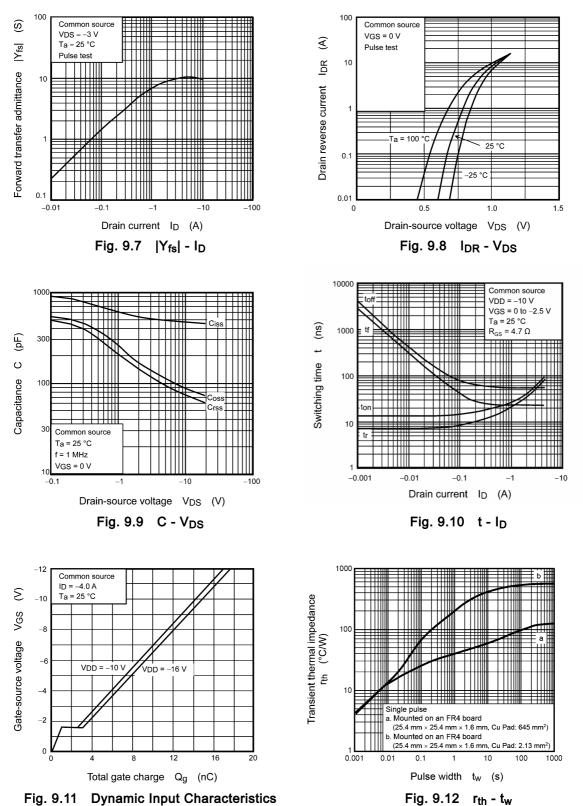


### 8. Internal Equivalent Circuit

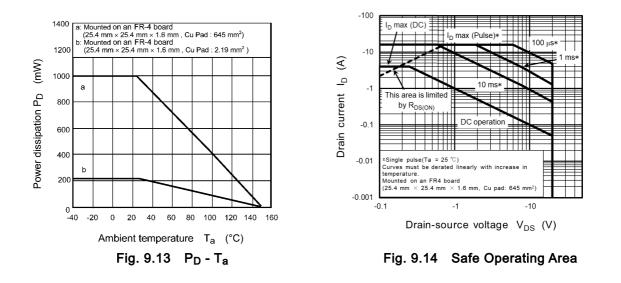


## 9. Characteristics Curves (Q1, Q2 Common) (Note)





rig. 5.11 Dynamic input characteristics



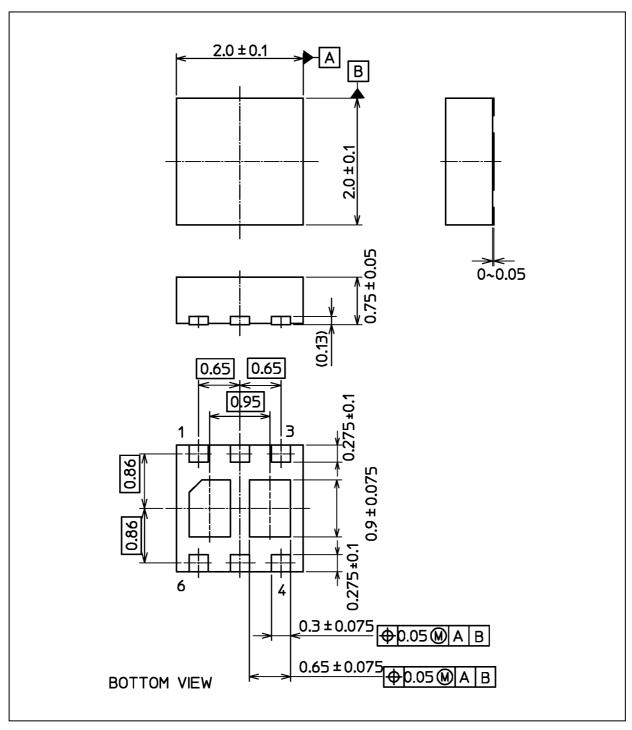
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## SSM6P49NU

#### **Package Dimensions**

Unit: mm



#### Weight: 8.5 mg (typ.)

|                 | Package Name(s) |
|-----------------|-----------------|
| JEDEC: SOT-1118 |                 |
| Nickname: UDFN6 |                 |

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